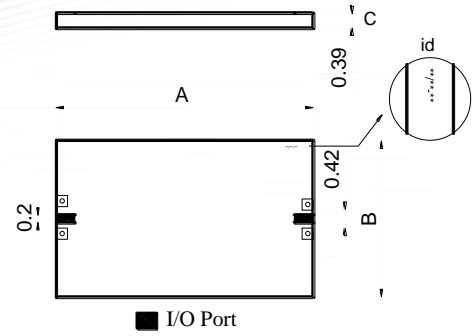


Thin Film ceramic Filter

BMBP18R757R5-8DA

Precautions

1. The chip is recommended sub-cavity use, both sides of the side wall from about 0.2mm, surface distance Cover about 3mm, the chip ports are interchangeable;
2. Chip recommended low-stress conductive adhesive (such as ME8456) bonding;
3. Chip should be installed in Kovar (recommended) or molybdenum copper with ceramic thermal expansion coefficient(6.7ppm / °C) on the carrier, the carrier thickness ≥ 0.2mm;
- 4 circuit board micro-chip wire bonding connection, it is recommended microstrip bonding at mining T-type structure to match, T-size as right



Circuit boardRogers 5880 , 10mil	Circuit boardRogers 4350, 10mi I
frequency: DC-38GHz	frequency: DC-32GHz
注: T 型图形顶端基板白边 50um; 频率 10GHz 以下无需匹配	

Features

- high-precision film processing technology
- high performance, low temperature drift, high power
- Ceramic substrate, 50Ω coplanar waveguide output
- Gold wire bonding, suitable for multi-chip integrated module applications

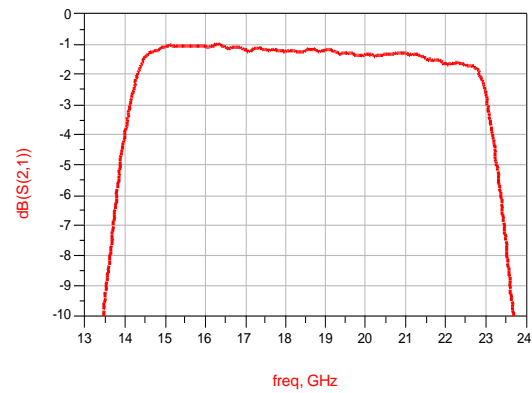
Environmental parameters

Working temperature	-55°C~+85°C
storage temperature	-55°C~+125°C
Maximum input power	35dBm

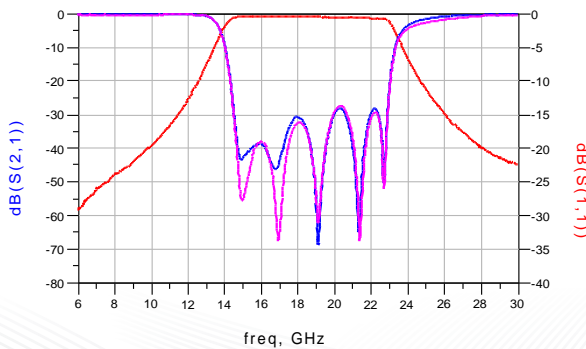
Electrical Specifications

Center frequency(f0)	18.7
Passband frequency range (GHz)	14.5-22.5
Band fluctuations (dB)	1
Center insertion loss (dB)	2.5
Return loss (dB)	15
Band attenuation (dB)	≥ 40@9.9GHz ≥ 40@28.1GHz

Passband loss VS frequency (T_A=25°C)



Band rejection & Return loss VS frequency (T_A=25°C)



Distal inhibition VS frequency (T_A=25°C)

